

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: Byung-Sup SHIM et al.

Serial No. 09/305,240

Examiner: O. Nadav

Filed: May 4, 1999

Group Art Unit: 2811

For: OPEN DRAIN INPUT/OUTPUT STRUCTURE AND  
MANUFACTURING METHOD THEREOF IN SEMICONDUCTOR  
DEVICE

Box CPA  
Assistant Commissioner for Patents  
Washington, D.C. 20231

PRELIMINARY AMENDMENT

Prior to examination, please amend the application as follows

IN THE SPECIFICATION

On page 2, line 25, replace "FIG.s" with --FIGs.--;

On page 4, line 9, replace "a n-type" with --an n-type--.

IN THE CLAIMS:

Please amend claim 9 as follows:

9. (Twice Amended) The transistor of claim 5, wherein the first sector  
is separated from the source region and from the drain region by substantially equal  
distances.

REMARKS

In this case, a Final Office Action was mailed on 8-31-2000. All pending  
claims [namely 5-7, 9] were rejected.

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Harrison

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